Titles of most frequently occurring classifications of patents returned from a search of 10598123 on Mar 09 , 2010

6 136/249 (4 OR, 2 XR)
Class 136 BATTERIES: THERMOELECTRIC AND PHOTOELECTRIC
136/243 .PHOTOELECTRIC
136/244 ..Panel or array
136/249 ...Monolithic semiconductor

4 365/201 (3 OR, 1 XR)
Class 365 STATIC INFORMATION STORAGE AND RETRIEVAL
365/189.011 .READ/WRITE CIRCUIT
365/201 ..Testing

3 438/396 (3 OR, 0 XR)
Class 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/381 .MAKING PASSIVE DEVICE (E.G., RESISTOR, CAPACITOR, ETC.)
438/396 ..Stacked capacitor

3 429/185 (0 OR, 3 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/122 .CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/163 ..Cell enclosure structure, e.g., housing, casing, container, cover, etc.
429/185 ...Having seal feature

3 438/933 (0 OR, 3 XR)
Class 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/933 .GERMANIUM OR SILICON OR GE-SI ON III-V

3 438/74 (1 OR, 2 XR)
Class 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/48 .MAKING DEVICE OR CIRCUIT RESPONSIVE TO NONELECTRICAL SIGNAL
438/57 ..Responsive to electromagnetic radiation
438/73 ...Making electromagnetic responsive array
438/74 ....Vertically arranged (e.g., tandem, stacked, etc.)

2 257/461 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
257/414 .RESPONSIVE TO NON-ELECTRICAL SIGNAL (E.G., CHEMICAL, STRESS, LIGHT, OR MAGNETIC FIELD SENSORS)
257/428 ..Electromagnetic or particle radiation
257/431 ...Light
257/461 ....Light responsive pn junction

2 712/15 (2 OR, 0 XR)
Class 712 ELECTRICAL COMPUTERS AND DIGITAL PROCESSING SYSTEMS: PROCESSING ARCHITECTURES AND INSTRUCTION PROCESSING (E.G., PROCESSORS)
712/1 .PROCESSING ARCHITECTURE
712/10 ..Array processor
712/11 ...Array processor element interconnection
712/15 ....Reconfiguring

2 438/970 (0 OR, 2 XR)
Class 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/970 .SPECIFIED ETCH STOP MATERIAL

2 257/E27.089 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE

DIODES)
257/E27.001 .DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE (EPO)
257/E27.009 ..Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Including integrated passive circuit elements (EPO)
257/E27.01 ...With semiconductor substrate only (EPO)
257/E27.07 ....Including a plurality of individual components in a repetitive configuration (EPO)
257/E27.081 .....Including field-effect component (EPO)
257/E27.084 ......Dynamic random access memory, DRAM, structure (EPO)
257/E27.085 ....One-transistor memory cell structure, i.e., each memory cell containing only one transistor (EPO)
257/E27.086 ....Storage electrode stacked over the transistor
257/E27.089 ....Storage electrode having multiple wings (EPO)

2 365/63 (0 OR, 2 XR)
Class 365 STATIC INFORMATION STORAGE AND RETRIEVAL
365/63 .INTERCONNECTION ARRANGEMENTS

2 438/586 (0 OR, 2 XR)
Class 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/584 .COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
438/585 ..Insulated gate formation
438/586 ...Combined with formation of ohmic contact to semiconductor region

2 257/E27.101 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
257/E27.001 .DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE (EPO)
257/E27.009 ..Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Including integrated passive circuit elements (EPO)
257/E27.01 ...With semiconductor substrate only (EPO)
257/E27.07 ....Including a plurality of individual components in a repetitive configuration (EPO)
257/E27.081 .....Including field-effect component (EPO)
257/E27.098 ......Static random access memory, SRAM, structure (EPO)
257/E27.101 ....Load element being a resistor (EPO)

2 429/59 (1 OR, 1 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/57 .SEALED CELL HAVING GAS PREVENTION OR ELIMATION MEANS
429/59 ..Prevention or elimination means is one of the cell electrodes or is electrically connected to an electrode

2 429/157 (1 OR, 1 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/122 .CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/149 ..Plural cells
429/156 ...Complete cells
429/157 ....In end-to-end contact, e.g., stacked button-type cell, etc.

2 429/162 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,

AND PROCESS
429/122 .CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/162 ..Flat-type unit cell and specific unit cell components

2 429/210 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/122 .CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/209 ..Electrode
429/210 ...Bipolar type

2 429/90 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/90 .WITH MEASURING, TESTING, OR INDICATING MEANS

2 429/217 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/122 .CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/209 ..Electrode
429/212 ...Having active material with organic component
429/217 ....Organic component is a binder

2 429/223 (1 OR, 1 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/122 .CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/209 ..Electrode
429/218.1 ...Chemically specified inorganic electrochemically active material containing
429/223 ....Nickel component is active material

2 257/E27.129 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
257/E27.001 .DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE (EPO)
257/E27.122 ..Including active semiconductor component sensitive to infrared radiation, light, or electromagnetic radiation of a shorter wavelength (EPO)
257/E27.127 ...Device controlled by radiation (EPO)
257/E27.128 ....With at least one potential barrier or surface barrier (EPO)
257/E27.129 .....In a repetitive configuration (EPO)

2 257/E31.115 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
257/E31.001 .SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF) (EPO)
257/E31.11 ..Detail of nonsemiconductor component of radiation-sensitive semiconductor device (EPO)
257/E31.113 ...Circuit arrangement of general character for device (EPO)
257/E31.114 ....For device having potential or surface barrier (EPO)

257/E31.115 .....Position-sensitive and lateral-effect photodetector (e.g., quadrant photodiode) (EPO)

2 257/E27.128 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
257/E27.001 .DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE (EPO)
257/E27.122 ..Including active semiconductor component sensitive to infrared radiation, light, or electromagnetic radiation of a shorter wavelength (EPO)
257/E27.127 ...Device controlled by radiation (EPO)
257/E27.128 ....With at least one potential barrier or surface barrier (EPO)

2 429/218.1 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/122 .CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/209 ..Electrode
429/218.1 ...Chemically specified inorganic electrochemically active material containing

2 716/8 (1 OR, 1 XR)
Class 716 DATA PROCESSING: DESIGN AND ANALYSIS OF CIRCUIT OR SEMICONDUCTOR MASK
716/1 .CIRCUIT DESIGN
716/8 ..Floorplanning

2 204/252 (0 OR, 2 XR)
Class 204 CHEMISTRY: ELECTRICAL AND WAVE ENERGY
204/193 .APPARATUS
204/194 ..Electrolytic
204/242 ...Cells
204/252 ....Diaphragm type

2 429/337 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
429/122 .CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
429/188 ..Include electrolyte chemically specified and method
429/324 ...Chemically specified organic solvent containing
429/336 ....Hetero ring in the organic solvent
429/337 .....Oxygen is the only ring hetero atom in the hetero ring (e.g., dioxolane, gamma butyrolactone, etc.)

2 438/73 (1 OR, 1 XR)
Class 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/48 .MAKING DEVICE OR CIRCUIT RESPONSIVE TO NONELECTRICAL SIGNAL
438/57 ..Responsive to electromagnetic radiation
438/73 ...Making electromagnetic responsive array

2 257/E25.007 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
257/E25.001 .ASSEMBLIES CONSISTING OF PLURALITY OF INDIVIDUAL SEMICONDUCTOR OR OTHER SOLID-STATE DEVICES (EPO)
257/E25.002 ..All devices being of same type, e.g., assemblies of rectifier diodes (EPO)
257/E25.003 ...Devices not having separate containers (EPO)

257/E25.004 ....Devices responsive or sensitive to electromagnetic radiation, e.g., infrared radiation, adapted for conversion of radiation into electrical energy or for control of electrical energy by such radiation (EPO)
257/E25.006 .....Stacked arrangements of devices (EPO)
257/E25.007 ......Devices being solar cells (EPO)

2 136/262 (0 OR, 2 XR)
Class 136 BATTERIES: THERMOELECTRIC AND PHOTOELECTRIC
136/243 .PHOTOELECTRIC
136/252 ..Cells
136/262 ...Gallium containing

2 257/E31.014 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
257/E31.001 .SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF) (EPO)
257/E31.002 ..Characterized by semiconductor body (EPO)
257/E31.003 ...Characterized by semiconductor body material (EPO)
257/E31.004 ....Inorganic materials (EPO)
257/E31.011 .....Including, apart from doping material or other impurity, only Group IV element (EPO)
257/E31.014 ......Characterized by doping material (EPO)

2 257/E31.021 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
257/E31.001 .SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF) (EPO)
257/E31.002 ..Characterized by semiconductor body (EPO)
257/E31.003 ...Characterized by semiconductor body material (EPO)
257/E31.004 ....Inorganic materials (EPO)
257/E31.019 .....Including, apart from doping material or other impurity, only Group III-V compound (EPO)
257/E31.02 ......For device having potential or surface barrier (EPO)
257/E31.021 ....Characterized by doping material GaAlAs, InGaAs, InGaAsP (EPO)

2 438/94 (0 OR, 2 XR)
Class 438 SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/48 .MAKING DEVICE OR CIRCUIT RESPONSIVE TO NONELECTRICAL SIGNAL
438/57 ..Responsive to electromagnetic radiation
438/93 ...Compound semiconductor
438/94 ....Heterojunction